

Part Number

Customer

Category	Parameter	Specification	Measurement Method
OverallWafer	1.0 Diameter	100.00 +/- 0.20 mm	Wafer Vendor
	2.0 Primary Flat Orientation	{110} +/- 1 degree	Wafer Vendor
	3.0 Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0 Secondary Flat Orientation	none / Semi standard	
	5.0 Secondary Flat Length	none / 18.5mm +/- 2.5mm	Wafer Vendor
	6.0 Overall Thickness	321.00 +/- 7.50 μ m	ADE, 100%
	7.0 Total Thickness Variation (TTV)	<5.00 μ m	Guaranteed by Process
	8.0 Bow	<80.00 μ m	ADE to ASTM F534, 20%
	9.0 Warp	<80.00 μ m	ADE to ASTM F657, 20%
	10.0 Edge Chips	0	Bright Light, 100% (note 2)
	11.0 Edge Exclusion	5mm	Guaranteed by process
HandleSilicon	12.0 Handle Growth Method	CZ	Wafer Vendor
	13.0 Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	14.0 Handle Thickness	130.00 +/- 5.00 μ m	ADE, 100%
	15.0 Handle Doping Type	P	Wafer Vendor
	16.0 Handle Dopant	Boron	Wafer Vendor
	17.0 Handle Resistivity	1 - 20 Ohmcm	Wafer Vendor
	18.0 Backside Finish	Polished with lasermarking and NO oxide.	Guaranteed by Process
BuriedOxide	19.0 Oxide Type	Thermal	
	20.0 Oxide Thickness	6,000.00 +/- 300.00 A	Nanospec centre point, 4%
	21.0 Oxide formed on	Device Wafer	
DeviceSilicon	22.0 Device Growth Method	CZ	Wafer Vendor
	23.0 Device Orientation	{100} +/- 1 degree	Wafer Vendor
	24.0 Nominal Thickness	120.00 +/- 1.00 μ m	FTIR, 100% 9-Pt (note3)
	25.0 Device Doping Type	P	Wafer Vendor
	26.0 Device Dopant	Boron	Wafer Vendor
	27.0 Device Resistivity	1 - 20 Ohmcm	Wafer Vendor
BuriedOxide2	28.0 Oxide 2 Type	Thermal	
	29.0 Oxide 2 Thickness	6,000.00 +/- 300.00 A	Nanospec centre point measurement, 4%
	30.0 Oxide 2 formed on	Device 2 wafer	Guaranteed by Process
DeviceSilicon2	31.0 Device 2 Growth Method	CZ	Wafer Vendor
	32.0 Device 2 Orientation	{100} +/- 1 degree	Wafer Vendor
	33.0 Device 2 Nominal Thickness	70.00 +/- 1.00 μ m	FTIR, 100% 9-point measurement (see note 3)
	34.0 Device 2 DopingType	P	Wafer Vendor
	35.0 Device 2 Dopant	Boron	Wafer Vendor

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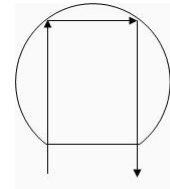
Customer

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DeviceSilicon2	36.0	Device 2 Resistivity	1 - 20 Ohmcm	Wafer Vendor
DeviceSilicon	37.0	Void	none	Wafer Vendor
	38.0	Scratches	0	Bright Light, 100% (note 2)
	39.0	Haze	none	Bright Light, 100% (note 2)

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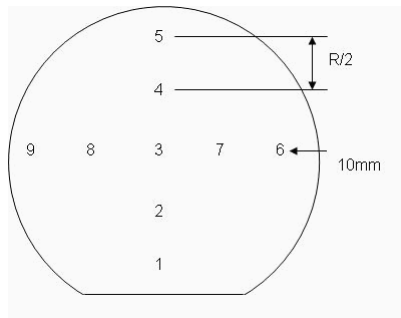
Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information